



# PMDPB56XNEA

30 V, dual N-channel Trench MOSFET

19 April 2016

Product data sheet

## 1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a small and leadless DFN2020D-6 (SOT1118D) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Leadless medium power SMD plastic package: 2 × 2 × 0.65 mm
- Tin-plated 100 % solderable side pads for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- AEC-Q101 qualified

## 3. Applications

- LED driver
- Power management
- Low-side loadswitch
- Switching circuits

## 4. Quick reference data

Table 1. Quick reference data

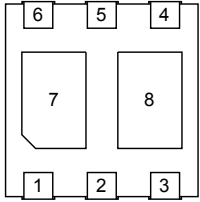
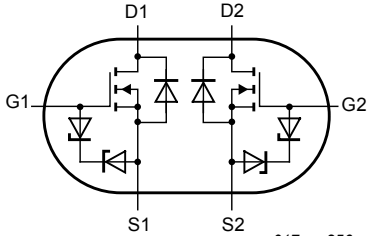
| Symbol   | Parameter                        | Conditions  | Min | Typ | Max | Unit |
|--|----------------------------------|---|-----|-----|-----|------|
| <b>Per transistor</b>                          |                                  |   |     |     |     |      |
| $V_{DS}$                                       | drain-source voltage             | $T_J = 25\text{ °C}$  | -   | -   | 30  | V    |
| $V_{GS}$                                       | gate-source voltage              |   | -12 | -   | 12  | V    |
| $I_D$  | drain current                    | $V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ °C}$                 | [1] | -   | 3.1 | A    |
| <b>Static characteristics (per transistor)</b> |                                  |   |     |     |     |      |
| $R_{DS(on)}$                                   | drain-source on-state resistance | $V_{GS} = 4.5\text{ V}; I_D = 3.1\text{ A}; T_J = 25\text{ °C}$ | -   | 55  | 72  | mΩ   |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

nexperia

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline   | Graphic symbol   |
|-----|--------|-------------|--|--|
| 1   | S1     | source TR1  |  <p>Transparent top view<br/><b>DFN2020D-6 (SOT1118D)</b></p> |  <p>017aaa256</p> |
| 2   | G1     | gate TR1    |  |  |
| 3   | D2     | drain TR2   |  |  |
| 4   | S2     | source TR2  |  |  |
| 5   | G2     | gate TR2    |  |  |
| 6   | D1     | drain TR1   |  |  |
| 7   | D1     | drain TR1   |  |  |
| 8   | D2     | drain TR2   |  |  |

## 6. Ordering information

Table 3. Ordering information

| Type number | Package    |   |          |
|-------------|------------|---|----------|
|             | Name       | Description   | Version  |
| PMDPB56XNEA | DFN2020D-6 | DFN2020D-6: plastic, thermally enhanced ultra thin and small outline package; no leads; 6 terminals; body 2 x 2 x 0.65 mm | SOT1118D |

## 7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PMDPB56XNEA | 3A           |

## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol                    | Parameter                                    | Conditions  |     | Min | Max  | Unit |
|---------------------------|--|---|-----|-----|------|------|
| <b>Per transistor</b>     |  |   |     |     |      |      |
| $V_{DS}$                  | drain-source voltage                         | $T_j = 25\text{ °C}$  |     | -   | 30   | V    |
| $V_{GS}$                  | gate-source voltage                          |   |     | -12 | 12   | V    |
| $I_D$                     | drain current                                | $V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ °C}$                                       | [1] | -   | 3.1  | A    |
|                           |  | $V_{GS} = 4.5\text{ V}; T_{amb} = 100\text{ °C}$                                      | [1] | -   | 2    | A    |
| $I_{DM}$                  | peak drain current                           | $T_{amb} = 25\text{ °C};$ single pulse; $t_p \leq 10\text{ }\mu\text{s}$              |     | -   | 12   | A    |
| $E_{DS(AL)S}$             | non-repetitive drain-source avalanche energy | $I_D = 0.3\text{ A}; T_{j(\text{init})} = 25\text{ °C};$ DUT in avalanche (unclamped) |     | -   | 6.2  | mJ   |
| $P_{tot}$                 | total power dissipation                      | $T_{amb} = 25\text{ °C}$  | [2] | -   | 485  | mW   |
|                           |  |   | [1] | -   | 1.15 | W    |
|                           |  | $T_{sp} = 25\text{ °C}$   |     | -   | 8.33 | W    |
| <b>Per device</b>         |  |   |     |     |      |      |
| $T_j$                     | junction temperature                         |   |     | -55 | 150  | °C   |
| $T_{amb}$                 | ambient temperature                          |   |     | -55 | 150  | °C   |
| $T_{stg}$                 | storage temperature                          |   |     | -65 | 150  | °C   |
| <b>Source-drain diode</b> |  |   |     |     |      |      |
| $I_S$                     | source current                               | $T_{amb} = 25\text{ °C}$  | [1] | -   | 1.1  | A    |
| <b>ESD Maximum rating</b> |  |   |     |     |      |      |
| $V_{ESD}$                 | electrostatic discharge voltage              | HBM   | [3] | -   | 2000 | V    |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain  $6\text{ cm}^2$ .

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.



Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100 \%$$



Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^\circ\text{C})}} \times 100 \%$$

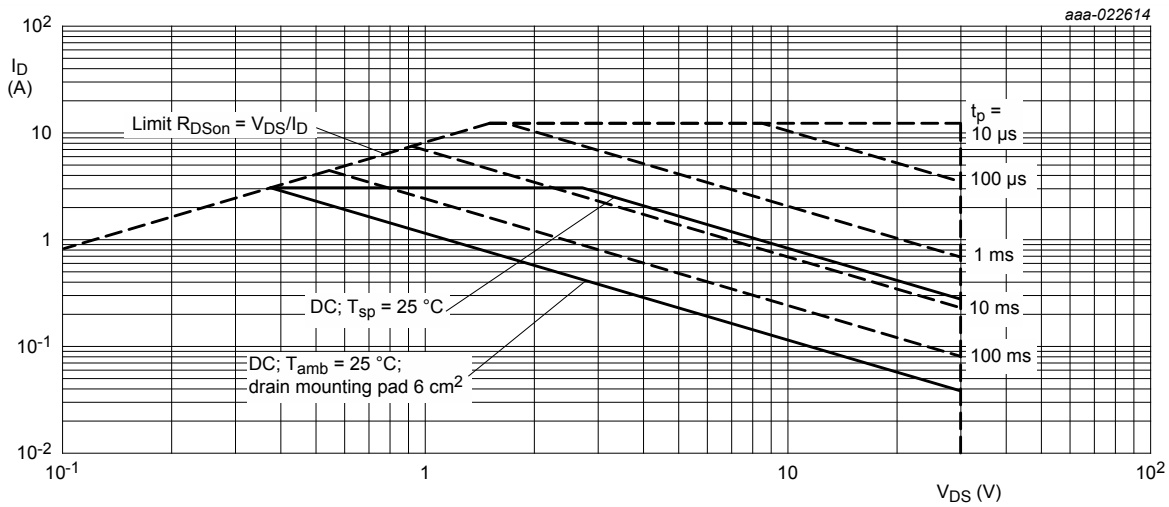


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

### 9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol                | Parameter  | Conditions  |     | Min | Typ | Max | Unit |
|-----------------------|--|-------------|-----|-----|-----|-----|------|
| <b>Per transistor</b> |  |             |     |     |     |     |      |
| $R_{th(j-a)}$         | thermal resistance from junction to ambient      | in free air | [1] | -   | 224 | 257 | K/W  |
|                       |  |             | [2] | -   | 96  | 109 | K/W  |
| $R_{th(j-sp)}$        | thermal resistance from junction to solder point |             |     | -   | 12  | 15  | K/W  |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

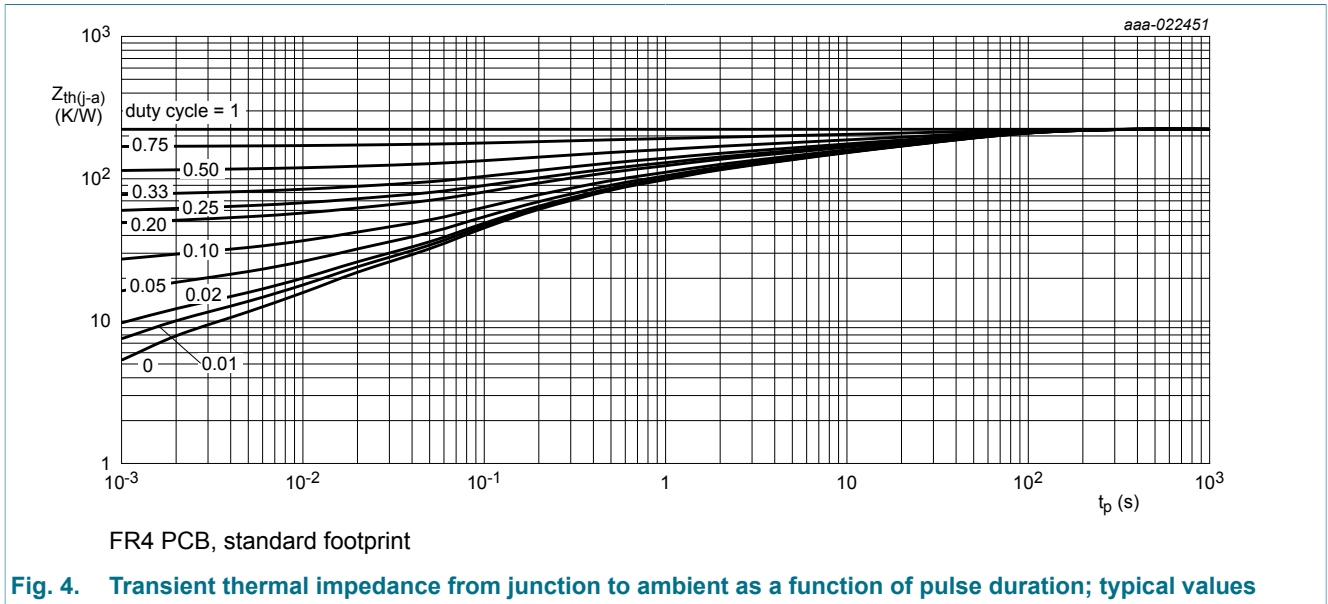
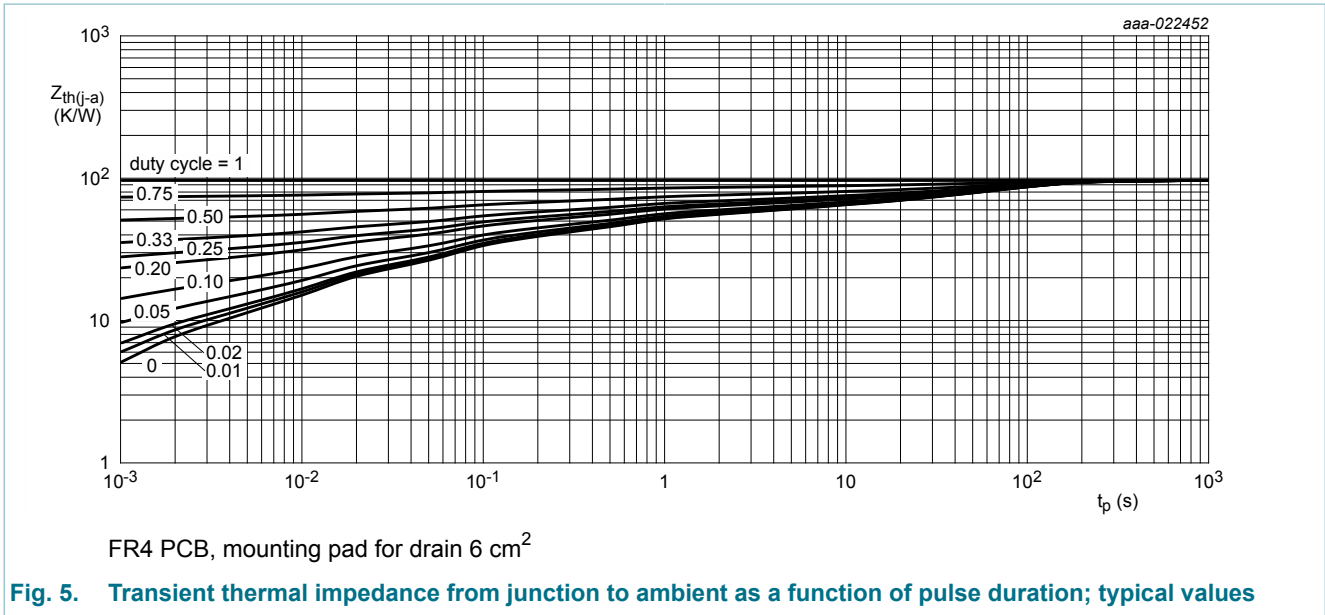


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



## 10. Characteristics

Table 7. Characteristics

| Symbol  | Parameter                        | Conditions  | Min  | Typ | Max  | Unit          |
|---|----------------------------------|---|--|-----|------|---------------|
| <b>Static characteristics (per transistor)</b>  |                                  |   |  |     |      |               |
| $V_{(BR)DSS}$                                   | drain-source breakdown voltage   | $I_D = 250 \mu\text{A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$                              | 30   | -   | -    | V             |
| $V_{GSth}$                                      | gate-source threshold voltage    | $I_D = 250 \mu\text{A}$ ; $V_{DS} = V_{GS}$ ; $T_j = 25 \text{ }^\circ\text{C}$                                   | 0.75   | 1   | 1.25 | V             |
| $I_{DSS}$                                       | drain leakage current            | $V_{DS} = 30 \text{ V}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$                              | -  | -   | 1    | $\mu\text{A}$ |
| $I_{GSS}$                                       | gate leakage current             | $V_{GS} = 12 \text{ V}$ ; $V_{DS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$                              | -  | -   | 10   | $\mu\text{A}$ |
|   |                                  | $V_{GS} = -12 \text{ V}$ ; $V_{DS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$                             | -  | -   | -10  | $\mu\text{A}$ |
|   |                                  | $V_{GS} = 4.5 \text{ V}$ ; $V_{DS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$                             | -  | -   | 2    | $\mu\text{A}$ |
|   |                                  | $V_{GS} = -4.5 \text{ V}$ ; $V_{DS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$                            | -  | -   | -2   | $\mu\text{A}$ |
| $R_{DSon}$                                      | drain-source on-state resistance | $V_{GS} = 4.5 \text{ V}$ ; $I_D = 3.1 \text{ A}$ ; $T_j = 25 \text{ }^\circ\text{C}$                              | -  | 55  | 72   | m $\Omega$    |
|   |                                  | $V_{GS} = 4.5 \text{ V}$ ; $I_D = 3.1 \text{ A}$ ; $T_j = 150 \text{ }^\circ\text{C}$                             | -  | 92  | 121  | m $\Omega$    |
|   |                                  | $V_{GS} = 2.5 \text{ V}$ ; $I_D = 2.6 \text{ A}$ ; $T_j = 25 \text{ }^\circ\text{C}$                              | -  | 72  | 102  | m $\Omega$    |
| $g_{fs}$  | forward transconductance         | $V_{DS} = 10 \text{ V}$ ; $I_D = 3.1 \text{ A}$ ; $T_j = 25 \text{ }^\circ\text{C}$                               | -  | 12  | -    | S             |
| $R_G$   | gate resistance                  | $f = 1 \text{ MHz}$ ; $T_j = 25 \text{ }^\circ\text{C}$   | -  | 9.2 | -    | $\Omega$      |
| <b>Dynamic characteristics (per transistor)</b> |                                  |   |  |     |      |               |
| $Q_{G(tot)}$                                    | total gate charge                | $V_{DS} = 15 \text{ V}$ ; $I_D = 3.1 \text{ A}$ ; $V_{GS} = 4.5 \text{ V}$ ;<br>$T_j = 25 \text{ }^\circ\text{C}$ | -  | 2.9 | 5    | nC            |
| $Q_{GS}$  | gate-source charge               |   | -  | 0.4 | -    | nC            |
| $Q_{GD}$  | gate-drain charge                |   | -  | 0.8 | -    | nC            |
| $C_{iss}$                                       | input capacitance                | $V_{DS} = 15 \text{ V}$ ; $f = 1 \text{ MHz}$ ; $V_{GS} = 0 \text{ V}$ ;<br>$T_j = 25 \text{ }^\circ\text{C}$     | -  | 256 | -    | pF            |
| $C_{oss}$                                       | output capacitance               |   | -  | 31  | -    | pF            |
| $C_{riss}$                                      | reverse transfer capacitance     |   | -  | 23  | -    | pF            |
| $t_{d(on)}$                                     | turn-on delay time               |   | $V_{DS} = 15 \text{ V}$ ; $I_D = 8 \text{ A}$ ; $V_{GS} = 4.5 \text{ V}$ ;<br>$R_{G(ext)} = 6 \text{ } \Omega$ ; $T_j = 25 \text{ }^\circ\text{C}$ | -   | 9    | -             |
| $t_r$   | rise time                        | -   |  | 20  | -    | ns            |
| $t_{d(off)}$                                    | turn-off delay time              | -   |  | 19  | -    | ns            |
| $t_f$   | fall time                        | -   |  | 7   | -    | ns            |
| <b>Source-drain diode (per transistor)</b>      |                                  |   |  |     |      |               |
| $V_{SD}$  | source-drain voltage             | $I_S = 1.1 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$                                | -  | 0.7 | 1.2  | V             |

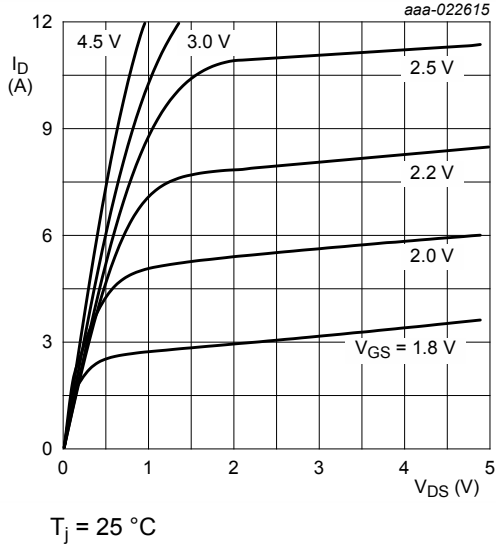


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

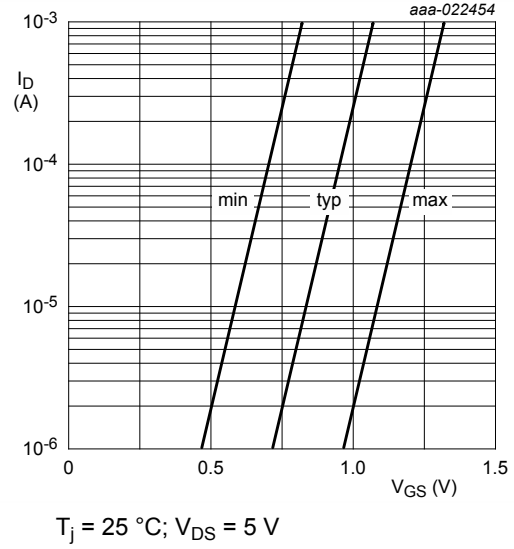


Fig. 7. Subthreshold drain current as a function of gate-source voltage

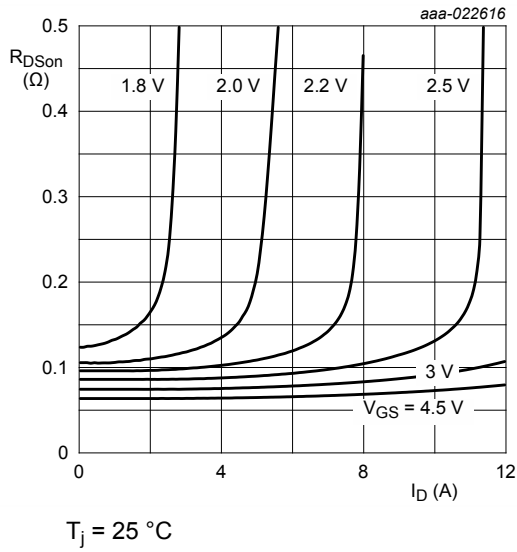


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

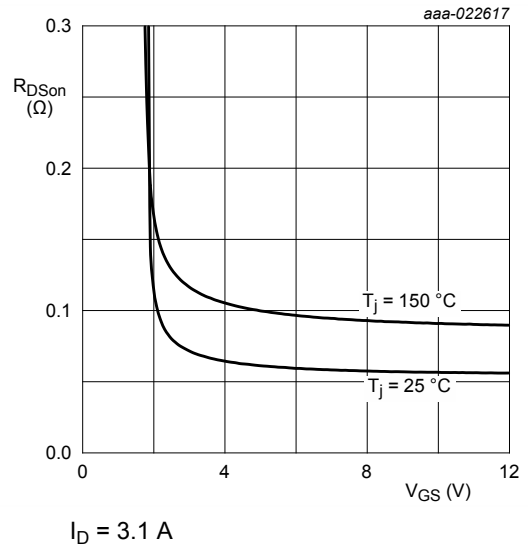
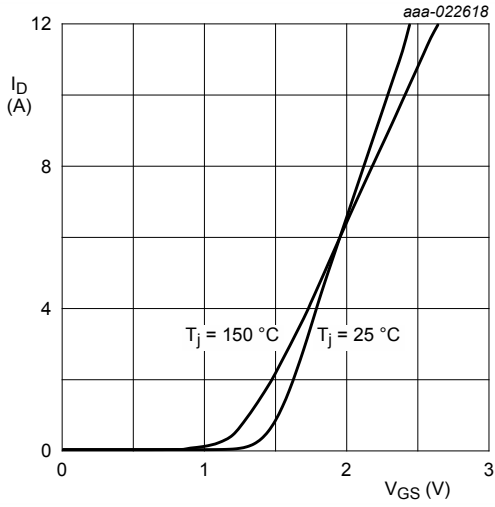


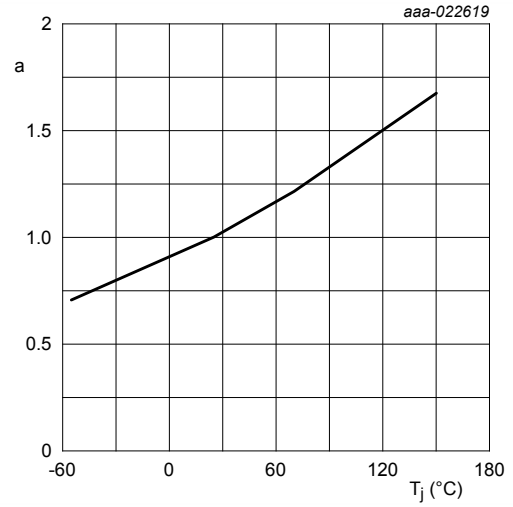
Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values





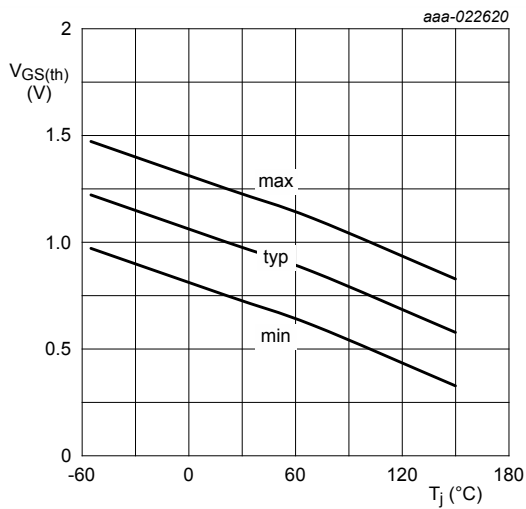
$$V_{DS} > I_D \times R_{DSon}$$

**Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values**



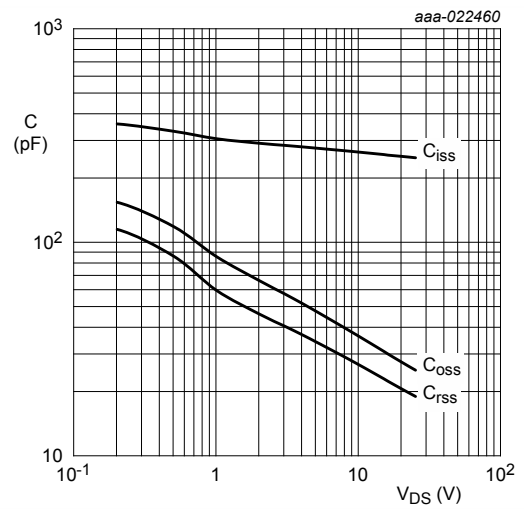
**Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values**

$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$



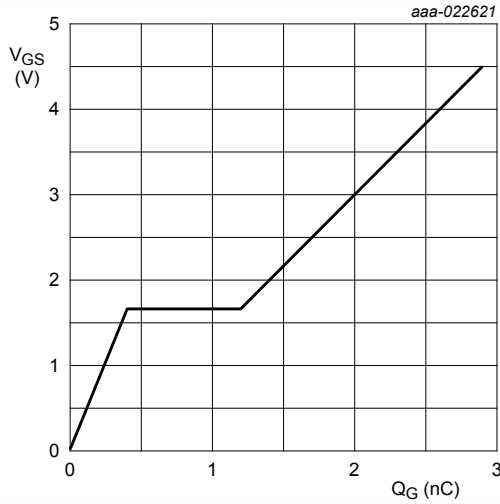
$$I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$$

**Fig. 12. Gate-source threshold voltage as a function of junction temperature**



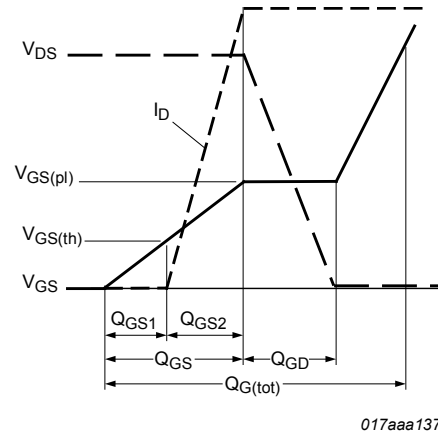
$$f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$$

**Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**

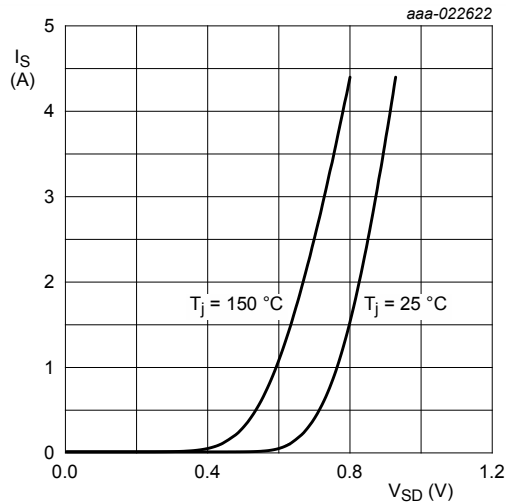


$I_D = 3.1\text{ A}$ ;  $V_{DS} = 15\text{ V}$ ;  $T_{amb} = 25\text{ }^\circ\text{C}$

**Fig. 14. Gate-source voltage as a function of gate charge; typical values**



**Fig. 15. Gate charge waveform definitions**



$V_{GS} = 0\text{ V}$

**Fig. 16. Source current as a function of source-drain voltage; typical values**

## 11. Test information

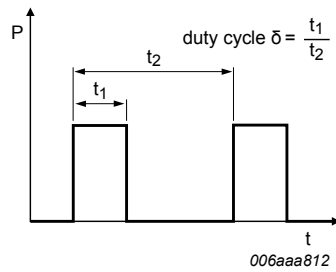


Fig. 17. Duty cycle definition

### 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

## 12. Package outline

DFN2020D-6: plastic, thermally enhanced ultra thin and small outline package; no leads; 6 terminals; body 2 x 2 x 0.65 mm

SOT1118D

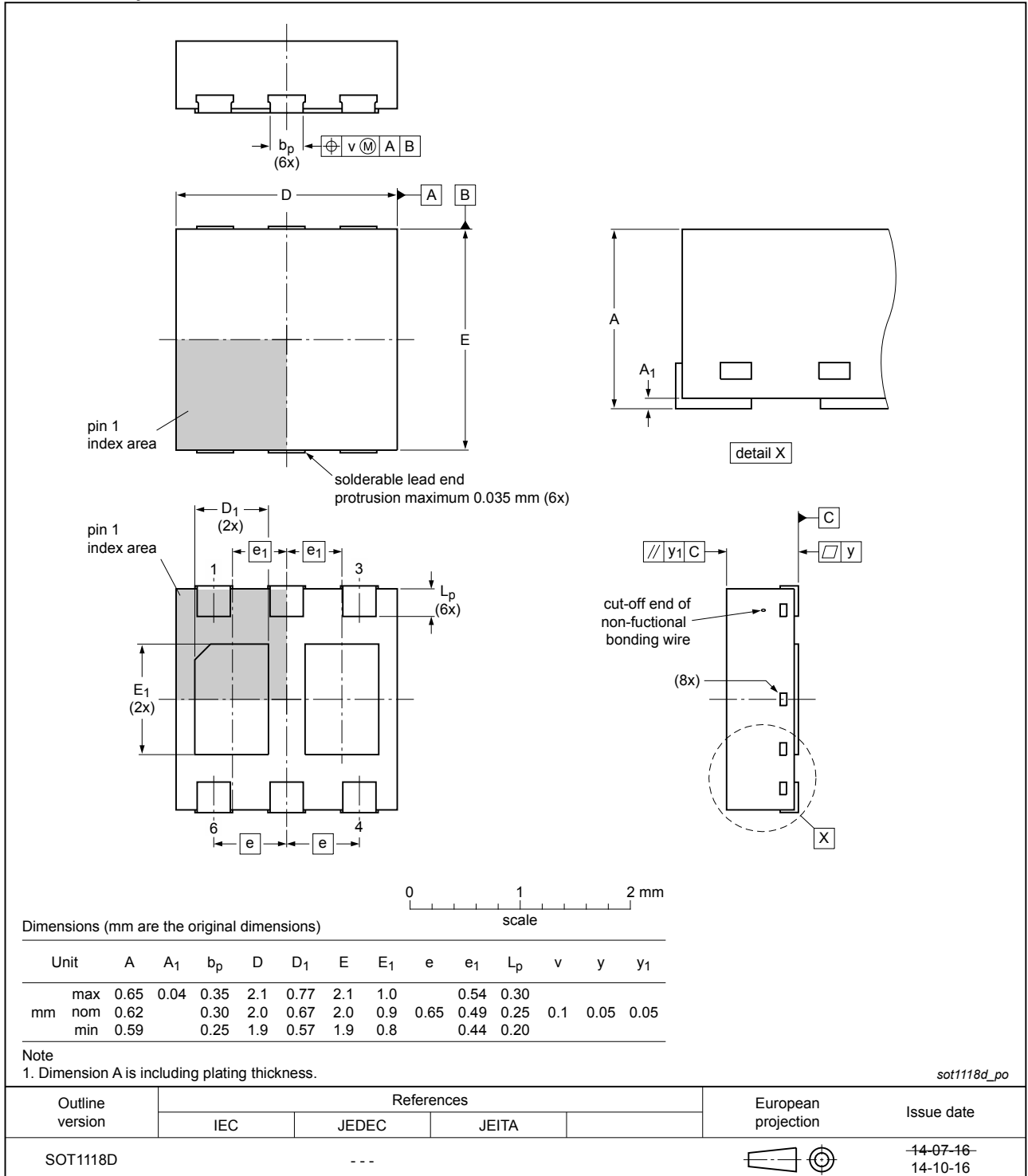
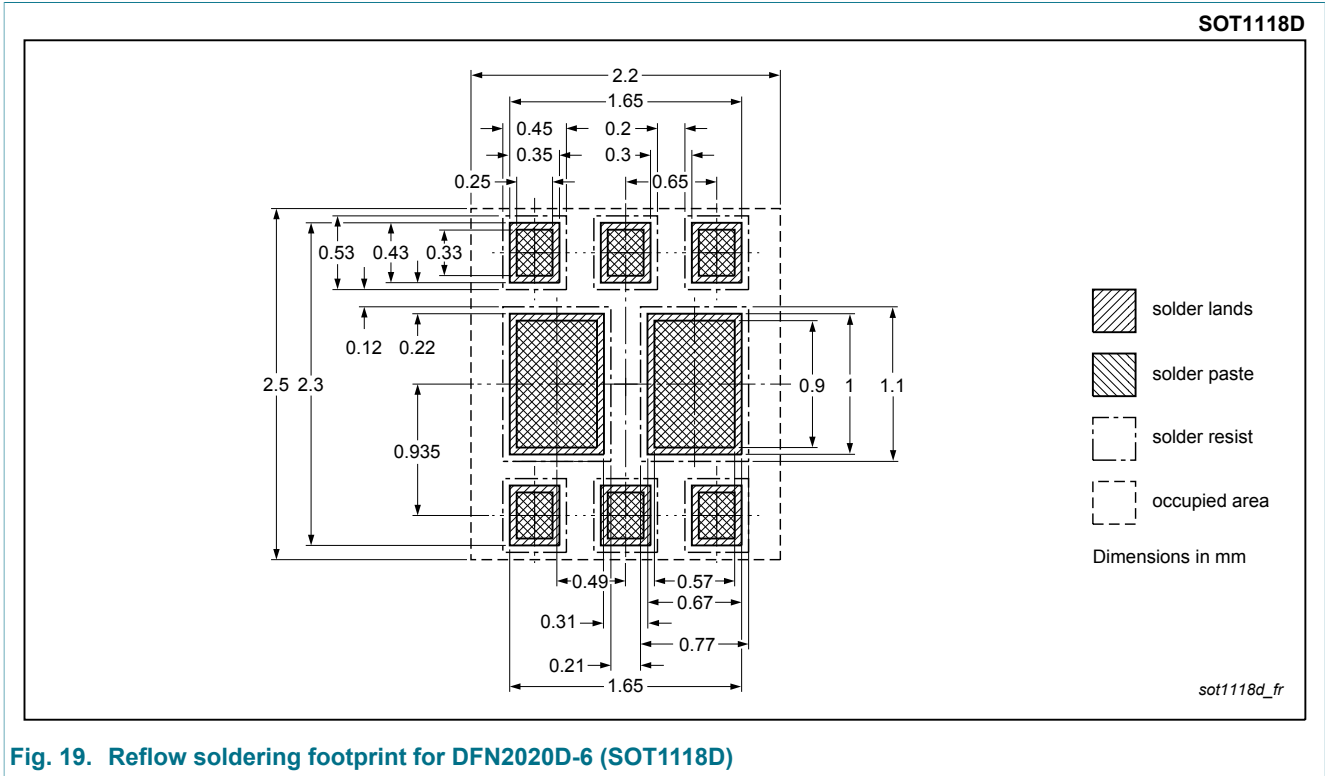


Fig. 18. Package outline DFN2020D-6 (SOT1118D)

### 13. Soldering



**Fig. 19. Reflow soldering footprint for DFN2020D-6 (SOT1118D)**

## 14. Revision history

Table 8. Revision history

| Data sheet ID   | Release date | Data sheet status  | Change notice | Supersedes |
|-----------------|--------------|--------------------|---------------|------------|
| PMDPB56XNEA v.1 | 20160419     | Product data sheet | -             | -          |

## 15. Legal information

### 15.1 Data sheet status

| Document status [1][2]         | Product status [3] | Definition  |
|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

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